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Docket No.: GR 98 P 2499 P

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By: Markus Noll

Date: August 6, 2002

Inventor : Thomas Peter Haneder et al.  
Applic. No. : 09/801,209  
Filed : March 7, 2001  
Title : Ferroelectric Transistor, Use Thereof In A Memory Cell  
Configuration And Method Of Producing The Ferroelectric Transistor  
Examiner : Thao X. Le - Art Unit: 2814

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## RESPONSE

Hon. Commissioner of Patents and Trademarks,  
Washington, D. C. 20231

Sir:

Responsive to the Office Action dated July 26, 2002, the following remarks are made:

In deference to the restriction requirement on pages 2 and 3 of the above-identified Office Action, applicants elect **group I**, claims 1-12 for prosecution at this time.

Applicants reserve the right to file a divisional application including the method claims of **group II** at a later date and/or to request a rejoinder under MPEP §821.04.

In view of the foregoing, the early issuance of an Action on the merits of claims is solicited.

Respectfully submitted,

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For Applicants

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REG. NO. 37,006

Date: August 6, 2002

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